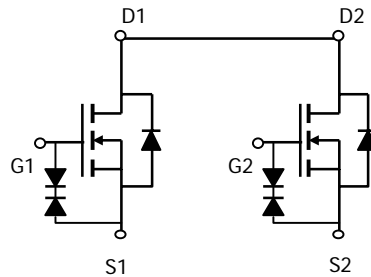
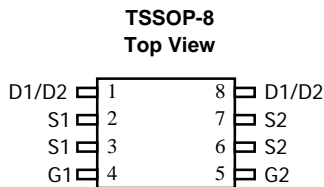


Common-Drain Dual N-Channel Enhancement Mode Field Effect Transistor

<p>General Description</p> <p>The AO8810 uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 1.8V. This device is suitable for use as a load switch or in PWM applications. It is ESD protected. <i>Standard Product AO8810 is Pb-free (meets ROHS & Sony 259 specifications). AO8810 is electrically identical.</i></p>	<p>Features</p> <p>V_{DS} (V) = 20V $I_D = 6A$ ($V_{GS} = 4.5V$) $R_{DS(ON)} < 22m\Omega$ ($V_{GS} = 4.5V$) $R_{DS(ON)} < 30m\Omega$ ($V_{GS} = 2.5V$) ESD Rating: 2000V HBM</p>
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Absolute Maximum Ratings $T_A=25^\circ C$ unless otherwise noted

Parameter	Symbol	Maximum	Units
Drain-Source Voltage	V_{DS}	20	V
Gate-Source Voltage	V_{GS}	± 8	V
Continuous Drain Current ^A	I_D	6	A
Pulsed Drain Current ^B			
Power Dissipation ^A	P_D	1.5	W
Junction and Storage Temperature Range	T_J, T_{STG}	-55 to 150	$^\circ C$

Thermal Characteristics

Parameter	Symbol	Typ	Max	Units
Maximum Junction-to-Ambient ^A	$R_{\theta JA}$	64	83	$^\circ C/W$
Maximum Junction-to-Ambient ^A		Steady-State	89	120
Maximum Junction-to-Lead ^C	$R_{\theta JL}$	53	70	$^\circ C/W$